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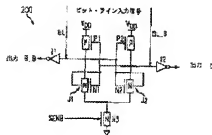
(54) CIRCUIT USING SOI TRANSISTOR AND METHOD
FOR REDUCING RESPONSE TIME OF SOI
TRANSISTOR

(57) Abstract:

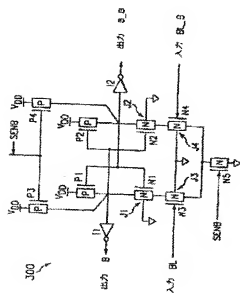
PROBLEM TO BE SOLVED: To improve a response time of amplifier using especially SOI in circuit constitution including a circuit element using SOI.

SOLUTION: Main bodies J1, J2 of differential input sense transistors N1, N2 using SOI technique are connected to respective gates of differential data input BL, BL-B, and pre-charge transistors P1, P2. Thereby, transistor turn-on voltage of the differential input sense transistors N1, N2 can be predicted, and response speed is increased.

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【図 3】



【図 4】

